

## N-Channel 100V(D-S) MOSFET

Product summary		
V <sub>DS</sub>	100	V
R <sub>DS(ON)</sub> (at V <sub>GS</sub> =10V) Typ.	110	mΩ
R <sub>DS(ON)</sub> (at V <sub>GS</sub> =4.5V) Typ.	160	mΩ
I <sub>D</sub> (T <sub>A</sub> =25°C)	3	A

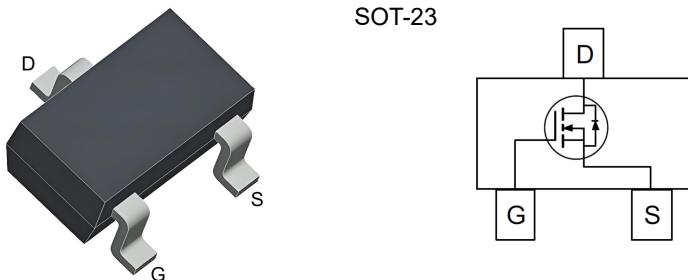
### Features

- Split Gate Trench MOSFET technology
- High density cell design for low R<sub>DS(ON)</sub>

### Applications

- DC-DC Converters
- Power management functions

### Pin Configuration



### Packing Information

Device	Package	Reel Size	Quantity(Min. Package)
ECDA03G10A	SOT-23	7"	3000pcs

### Absolute Maximum Ratings (at T<sub>A</sub>=25°C Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	100	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Continuous Drain Current <sup>A</sup>	T <sub>A</sub> =25°C	A
		T <sub>A</sub> =70°C	A
I <sub>DM</sub>	Pulse Drain Current Tested <sup>B</sup>	12	A
P <sub>D</sub>	Power Dissipation <sup>A</sup>	T <sub>A</sub> =25°C	W
T <sub>J, STG</sub>	Junction and Storage Temperature Range	-55 to +150	°C

### Thermal Characteristics

Symbol	Parameter	Typical	Units
R <sub>θJA</sub>	Thermal Resistance-Junction to ambient <sup>A</sup>	104	°C/W

Electrical Characteristics (at  $T_J = 25^\circ\text{C}$  Unless Otherwise Noted)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
<b>Static Parameters</b>						
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	100	--	--	V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}}=100\text{V}, V_{\text{GS}}=0\text{V}$	--	--	1	$\mu\text{A}$
$I_{\text{GSS}}$	Gate-Body Leakage Current	$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=\pm 20\text{V}$	--	--	$\pm 100$	nA
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1.0	1.8	3.0	V
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance <sup>B</sup>	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=3\text{A}$	--	110	140	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=2\text{A}$	--	160	200	$\Omega$
$V_{\text{SD}}$	Diode Forward Voltage	$I_{\text{S}}=3\text{A}, V_{\text{GS}}=0\text{V}$	--	--	1.3	V
<b>Dynamic Parameters <sup>C</sup></b>						
$C_{\text{iss}}$	Input Capacitance	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=50\text{V}$ $f=1\text{MHz}$	--	206	--	pF
$C_{\text{oss}}$	Output Capacitance		--	29	--	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance		--	1.4	--	pF
$Q_g$	Total Gate Charge	$V_{\text{DS}}=50\text{V}, I_{\text{D}}=3\text{A}$ $V_{\text{GS}}=10\text{V}$	--	4.3	--	nC
$Q_{\text{gs}}$	Gate-Source Charge		--	1.5	--	nC
$Q_{\text{gd}}$	Gate-Drain Charge		--	1.1	--	nC
$t_{\text{D}(\text{on})}$	Turn-on Delay Time	$V_{\text{DD}}=50\text{V}$ $I_{\text{D}}=3\text{A}, R_{\text{GEN}}=2\Omega$ , $V_{\text{GS}}=10\text{V}$	--	14.7	--	ns
$t_r$	Turn-on Rise Time		--	3.5	--	ns
$t_{\text{D}(\text{off})}$	Turn-off Delay Time		--	20.9	--	ns
$t_f$	Turn-off Fall Time		--	2.7	--	ns
$t_{\text{rr}}$	Reverse recovery time	$I_{\text{F}}=3\text{A}$ , $di/dt=100\text{A}/\mu\text{s}$	--	32	--	ns
$Q_{\text{rr}}$	Reverse recovery charge		--	39	--	nC

A. The data tested by surface mounted on a 1 inch x 1 inch FR-4 board with 2OZ copper.

B. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$ .

C. Guaranteed by design, not subject to production testing.

## Typical Characteristics

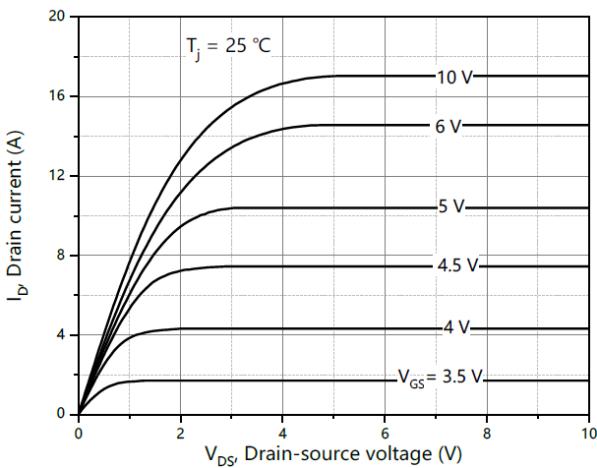


Figure1. Output Characteristics

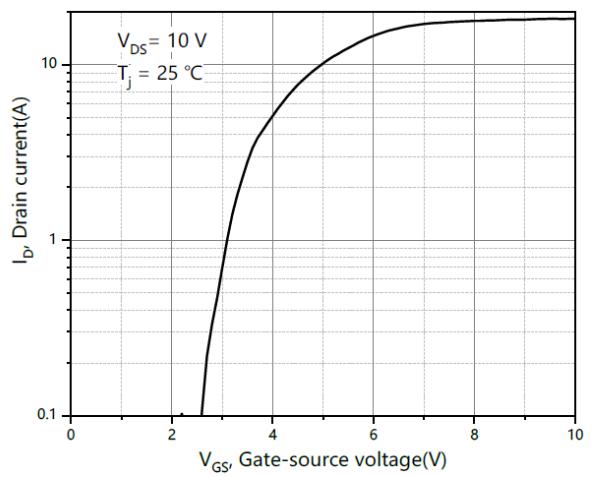


Figure2. Transfer Characteristics

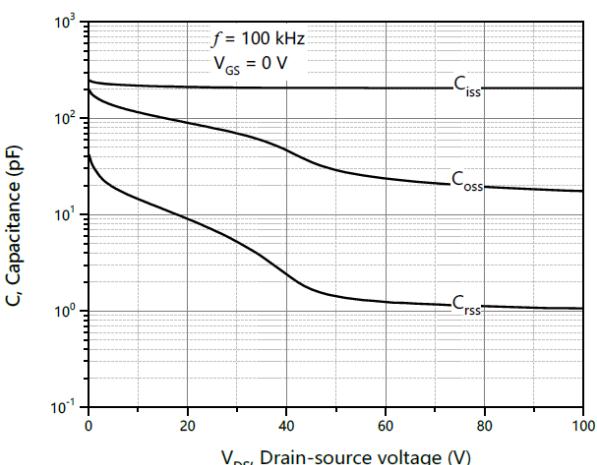


Figure3. Capacitance Characteristics

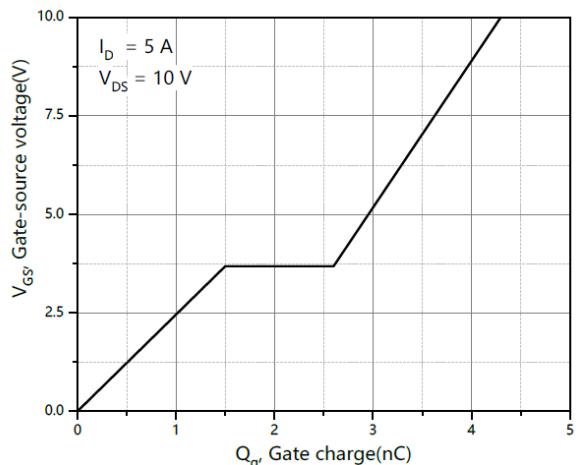


Figure4. Gate Charge

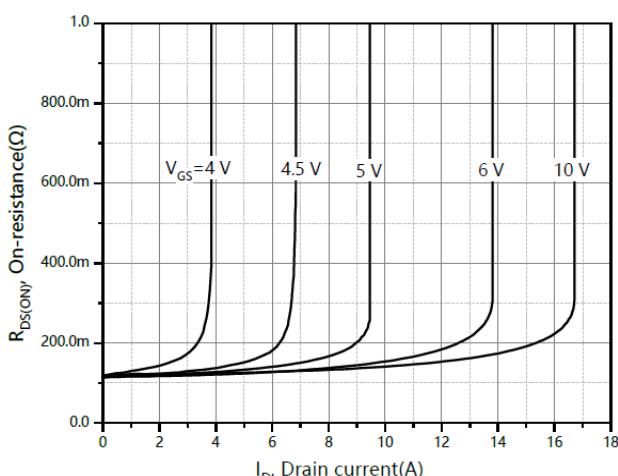


Figure5. : On-Resistance vs. Drain Current and Gate Voltage

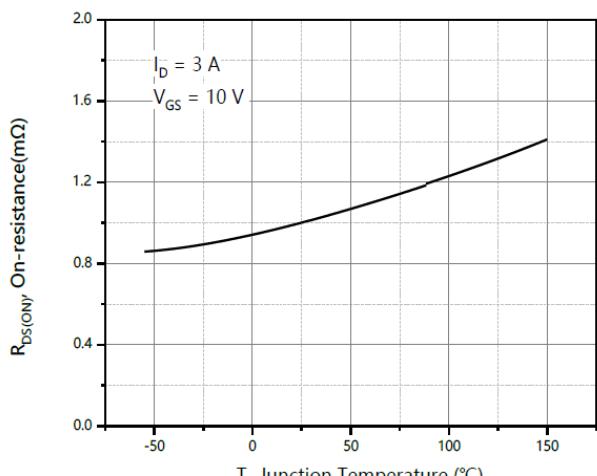
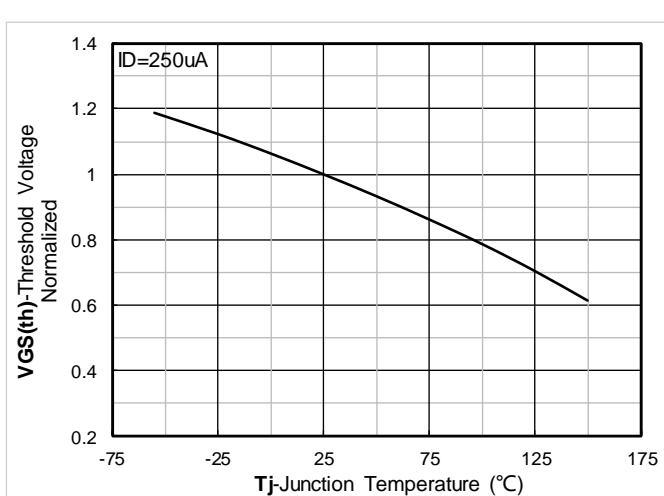
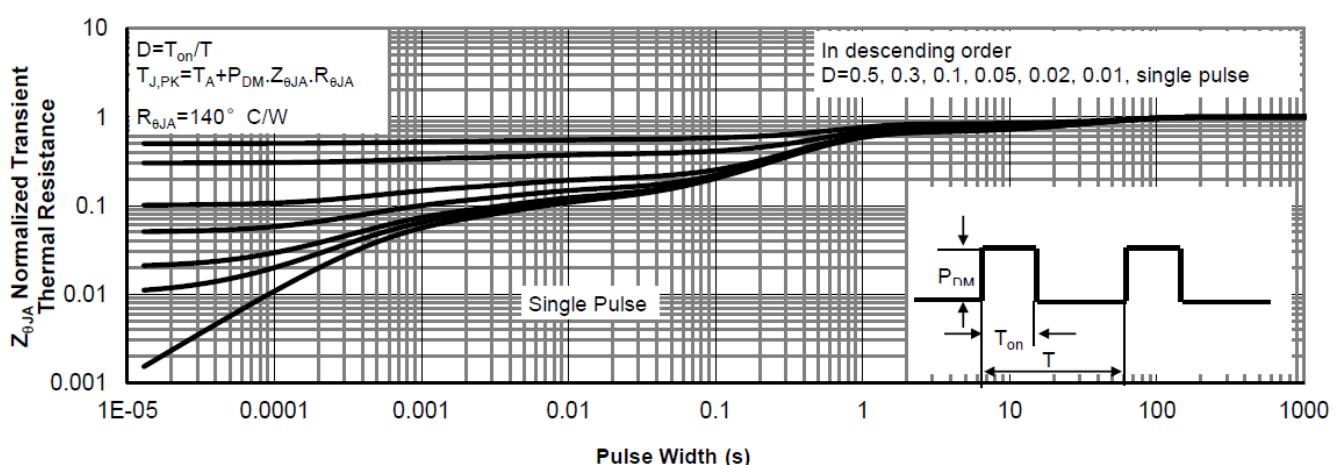
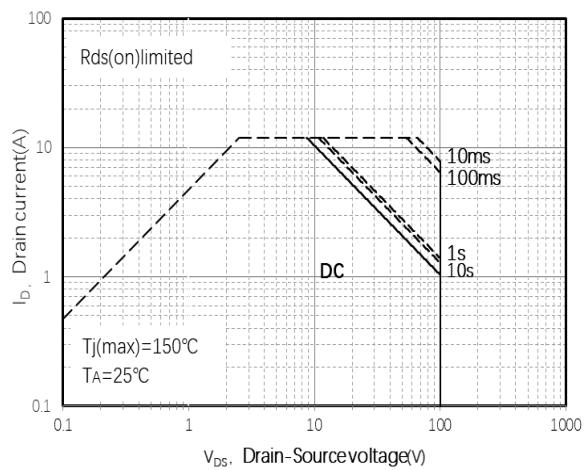
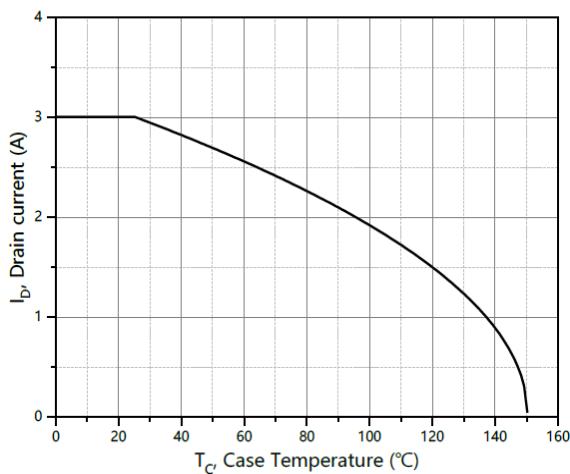
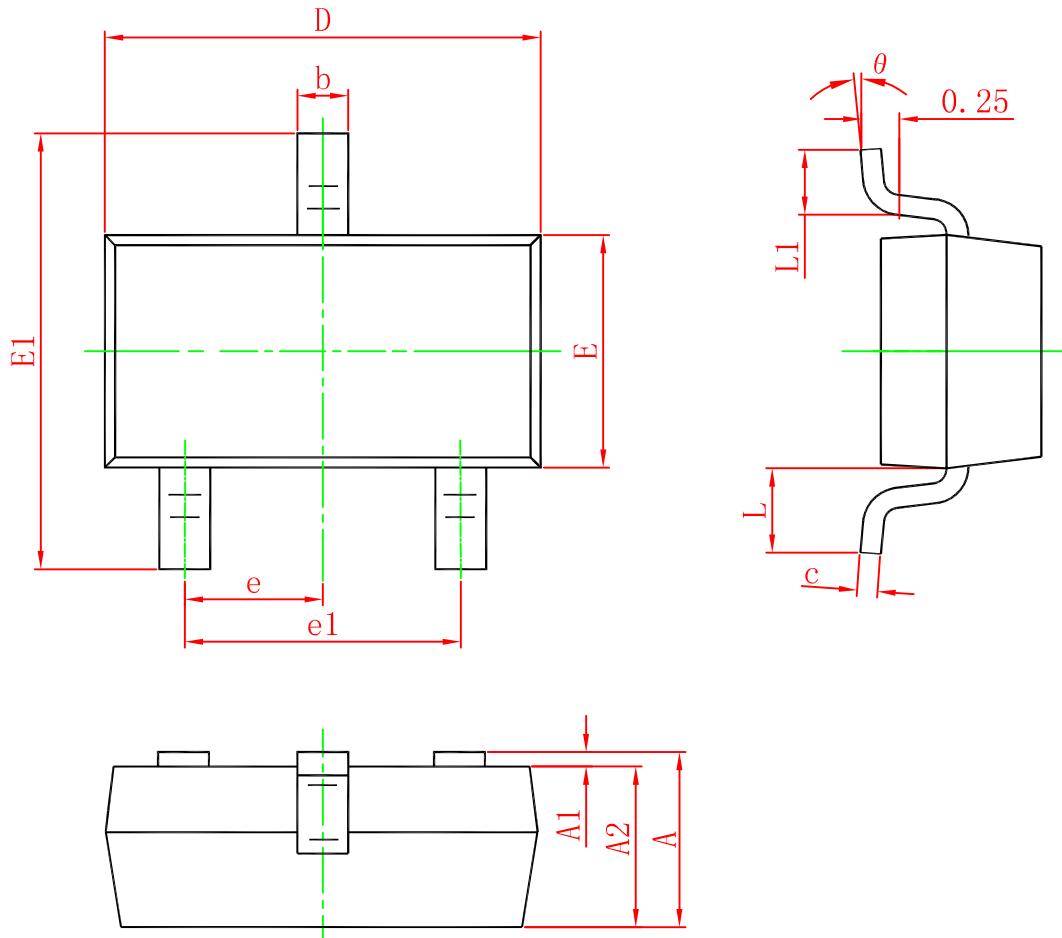


Figure6.Normalized On-Resistance

## Typical Characteristics



**SOT-23 Package Information**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°